

REMARKS

This paper is in response to the official action of October 18, 2005.
Reconsideration is requested.

By the foregoing amendments, the word "form" has been replaced with "from" in claim 1, line 9 in response to the objection to claim 1. The limitations of claim 3 have been incorporated into claim 1, and claim 3 has been canceled, as has non-elected claim 10.

No new matter has been added.

Reconsideration of the application as amended is solicited.

The anticipation rejection of claims 1, 3-5, 7, and 8 based on Meador et al., and the respective obviousness rejection of claims 2, 6, and 9 involving the Meador reference are respectfully but strongly traversed. Reconsideration is requested.

Reference is made to the following figure comparing the invention and the disclosure of Meador et al.

Invention	Meador et al.
Gas protection film	Photoresist
Photoresist layer	Middle layer
Etching mask layer	BARC
Underlying layer	Substrate

The invention is characterized by using a tri-layer resist process which comprises a gas protection film coated on a photoresist film while the tri-layer system of Meador et al. comprises a middle layer as an etch masking layer under a photoresist layer.

While a gas protection film of the present invention comprises a water-soluble polymer material so as to absorb silicon gas generated from the photoresist film, Meador et al. neither disclose nor suggest such a film absorbing gas generated from the photoresist film.

As a result, the Meador et al. disclosure does not anticipate any of claims 1, 3-5, 7, and 8.

Further, Hayase et al. U.S. 5,702,776 discloses that an organic polysilane absorbs UV energy, breaking the Si-Si bond therein, and then oxides by absorbing oxygen and moisture (col. 4 lines 9~12).

Finally, while an etching mask layer of the invention (claim 2) is formed by using the i-line photoresist and KrF photoresist, the etch masking layer of Meador et al. is a middle layer and contains silicon.

In view of the above-mentioned particulars, it is submitted that the present invention is substantially different from Meador et al. and that the secondary references do not supply the deficiencies of Meador et al.

Should the examiner wish to discuss the foregoing or any matter of form in an effort to advance this application towards allowance, he is urged to telephone the undersigned at the indicated number.

Respectfully submitted,

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By: 

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